

WHAT IS CLAIMED IS:

1. A method of manufacturing a semiconductor device,
comprising the steps of:

electrically isolating a diode formation region on a
5 semiconductor substrate by an element isolation layer;

holding, in a vacuum chamber, said semiconductor
substrate at which said element isolation layer is formed and
an impurity solid including impurity to be introduced into
said diode formation region;

10 introducing inert or reactive gas into said vacuum
chamber to generate plasma composed of said inert or reactive
gas;

applying to said impurity solid a first voltage which
allows said impurity solid to serve as a cathode for said
15 plasma, performing sputtering of said impurity solid by ions
in said plasma, and thereby mixing said impurity in said
impurity solid into said plasma;

applying to said semiconductor substrate held in said
vacuum chamber a second voltage which allows said
20 semiconductor substrate to serve as a cathode for said plasma
to cause a potential difference between said plasma and said

semiconductor substrate so that said impurity mixed into said plasma is introduced directly to a surface portion of said diode formation region at said semiconductor substrate to form an impurity layer; and

5 forming, on said semiconductor substrate at which said impurity layer is formed, an interconnection layer electrically connected to said impurity layer.

2. The method of manufacturing a semiconductor device
10 of claim 1, wherein

said step of introducing said impurity within said plasma onto the surface of the diode formation region of said semiconductor substrate includes, a process of irradiation of a laser beam on said semiconductor substrate.

15 3. The method of manufacturing a semiconductor device
of claim 1, wherein

said impurity layer includes components of said inert or reactive gas.

20 4. The method of manufacturing a semiconductor device
of claim 3, wherein

concentration of the components of said inert or reactive gas exceeds $1 \times 10^{20} \text{ cm}^{-3}$.

5. The method of manufacturing a semiconductor device of
claim 1, wherein

each of said first and second voltages is a negative
voltage.

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6. The method of manufacturing a semiconductor device of
claim 1, wherein

10 said semiconductor substrate is composed of silicon,
 said impurity is arsenic, phosphorus, boron, aluminum,
 antimony, gallium, or indium, and
 said inert or reactive gas is gas including nitrogen or
 argon.

7. A method of manufacturing a semiconductor device,
15 comprising the steps of:

 electrically isolating a diode formation region on a
 semiconductor substrate by an element isolation layer;
 holding, in a vacuum chamber, said semiconductor
 substrate at which said element isolation layer is formed and
 20 an impurity solid including impurity to be introduced into
 said diode formation region;

introducing inert or reactive gas into said vacuum chamber to generate plasma composed of said inert or reactive gas;

applying to said impurity solid a first voltage which 5 allows said impurity solid to serve as a cathode for said plasma, performing sputtering of said impurity solid by ions in said plasma, and thereby mixing said impurity in said impurity solid into said plasma;

applying to said semiconductor substrate held in said 10 vacuum chamber a second voltage which allows said semiconductor substrate to serve as an anode for said plasma to cause a potential difference between said plasma and said semiconductor substrate so that said impurity mixed into said plasma is introduced directly to a surface portion of said 15 diode formation region at said semiconductor substrate to form an impurity layer; and

forming, on said semiconductor substrate at which said impurity layer is formed, an interconnection layer electrically connected to said impurity layer.

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8. The method of manufacturing a semiconductor device of claim 7, wherein

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said step of introducing said impurity within said plasma onto the surface of the diode formation region of said semiconductor substrate includes, a process of irradiation of a laser beam on said semiconductor substrate.

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9. The method of manufacturing a semiconductor device of claim 7, wherein

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said impurity layer includes components of said inert or reactive gas.

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10. The method of manufacturing a semiconductor device of claim 9, wherein

concentration of the components of said inert or reactive gas exceeds $1 \times 10^{20} \text{ cm}^{-3}$.

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11. The method of manufacturing a semiconductor device of claim 7, wherein

said first voltage is a negative voltage.

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12. The method of manufacturing a semiconductor device of claim 7, wherein

said second voltage is a voltage of 0 V or lower.

13. The method of manufacturing a semiconductor device
of claim 7, wherein

said semiconductor substrate is composed of silicon,

5 said impurity is arsenic, phosphorus, boron, aluminum,
antimony, gallium, or indium, and

said inert or reactive gas is gas including nitrogen or
argon.

14. A method of manufacturing a semiconductor device,
10 comprising the steps of:

electrically isolating a diode formation region on a
semiconductor substrate by an element isolation layer;

15 holding, in a vacuum chamber, said semiconductor
substrate at which said element isolation layer is formed and
an impurity solid including impurity to be introduced into
said diode formation region;

introducing inert or reactive gas into said vacuum
chamber to generate plasma composed of said inert or reactive
gas;

20 applying to said impurity solid a first voltage which
allows said impurity solid to serve as an anode for said

plasma, performing sputtering of said impurity solid by ions in said plasma, and thereby mixing said impurity in said impurity solid into said plasma;

applying to said semiconductor substrate held in said
5 vacuum chamber a second voltage which allows said semiconductor substrate to serve as an anode for said plasma to cause a potential difference between said plasma and said semiconductor substrate so that said impurity mixed into said plasma is introduced directly to a surface portion of said
10 diode formation region at said semiconductor substrate to form an impurity layer; and

forming, on said semiconductor substrate at which said impurity layer is formed, an interconnection layer electrically connected to said impurity layer.

15 15. The method of manufacturing a semiconductor device of claim 14, wherein

 said step of introducing said impurity within said plasma onto the surface of the diode formation region of said
20 semiconductor substrate includes, a process of irradiation of a laser beam on said semiconductor substrate.

16. The method of manufacturing a semiconductor device

of claim 14, wherein

said impurity layer includes components of said inert or reactive gas.

5 17. The method of manufacturing a semiconductor device
of claim 16, wherein

concentration of the components of said inert or reactive gas exceeds $1 \times 10^{20} \text{ cm}^{-3}$.

10 18. The method of manufacturing a semiconductor device
of claim 14, wherein

each of said first and second voltages is a voltage of 0 V or lower.

15 19. The method of manufacturing a semiconductor device
of claim 14, wherein

said semiconductor substrate is composed of silicon,

said impurity is arsenic, phosphorus, boron, aluminum,
antimony, gallium, or indium, and

20 said inert or reactive gas is gas including nitrogen or argon.

20. A method of manufacturing a semiconductor device,
comprising the steps of:

electrically isolating a transistor formation region on a
semiconductor substrate by an element isolation layer;

5 forming an electrode at said transistor formation region
on said semiconductor substrate at which said element
isolation layer is formed, with an insulating layer
interposed therebetween;

10 holding, in a vacuum chamber, said semiconductor
substrate at which said electrode is formed and an impurity
solid including impurity to be introduced into said
transistor formation region;

15 introducing inert or reactive gas into said vacuum
chamber to generate plasma composed of said inert or reactive
gas;

applying to said impurity solid a first voltage which
allows said impurity solid to serve as a cathode for said
plasma, performing sputtering of said impurity solid by ions
in said plasma, and thereby mixing said impurity in said
20 impurity solid into said plasma;

applying to said semiconductor substrate held in said

vacuum chamber a second voltage which allows said
semiconductor substrate to serve as a cathode for said plasma
to cause a potential difference between said plasma and said
semiconductor substrate so that said impurity mixed into said
plasma is introduced directly to a surface portion of said
transistor formation region at said semiconductor substrate
to form an impurity layer; and

forming, on said semiconductor substrate at which said
impurity layer is formed, an interconnection layer
10 electrically connected to said impurity layer.

21. The method of manufacturing a semiconductor device
of claim 20, wherein

said step of introducing said impurity within said
15 plasma onto the surface of the diode formation region of said
semiconductor substrate includes, a process of irradiation of
a laser beam on said semiconductor substrate.

22. The method of manufacturing a semiconductor device
20 of claim 20, wherein

said impurity layer includes components of said inert or
reactive gas.

23. The method of manufacturing a semiconductor device
of claim 22, wherein

concentration of the components of said inert or
reactive gas exceeds $1 \times 10^{20} \text{ cm}^{-3}$.

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24. The method of manufacturing a semiconductor device
of claim 20, wherein

each of said first and second voltages is a negative
voltage.

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25. The method of manufacturing a semiconductor device
of claim 20, wherein

said semiconductor substrate is composed of silicon,

said impurity is arsenic, phosphorus, boron, aluminum,

15 antimony, gallium, or indium, and

said inert or reactive gas is gas including nitrogen or
argon.

20 26. A method of manufacturing a semiconductor device,
comprising the steps of:

electrically isolating a transistor formation region on a

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- semiconductor substrate by an element isolation layer;
- forming an electrode at said transistor formation region on said semiconductor substrate at which said element isolation layer is formed, with an insulating layer
- 5 interposed therebetween;
- holding, in a vacuum chamber, said semiconductor substrate at which said electrode is formed and an impurity solid including impurity to be introduced into said transistor formation region;
- 10 introducing inert or reactive gas into said vacuum chamber to generate plasma composed of said inert or reactive gas;
- applying to said impurity solid a first voltage which allows said impurity solid to serve as a cathode for said
- 15 plasma, performing sputtering of said impurity solid by ions in said plasma, and thereby mixing said impurity in said impurity solid into said plasma;
- applying to said semiconductor substrate held in said vacuum chamber a second voltage which allows said
- 20 semiconductor substrate to serve as an anode for said plasma to cause a potential difference between said plasma and said

semiconductor substrate so that said impurity mixed into said plasma is introduced directly to a surface portion of said transistor formation region at said semiconductor substrate to form an impurity layer; and

5 forming, on said semiconductor substrate at which said impurity layer is formed, an interconnection layer electrically connected to said impurity layer.

27. The method of manufacturing a semiconductor device

10 of claim 26, wherein

said step of introducing said impurity within said plasma onto the surface of the diode formation region of said semiconductor substrate includes, a process of irradiation of a laser beam on said semiconductor substrate.

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28. The method of manufacturing a semiconductor device of claim 26, wherein

said impurity layer includes components of said inert or reactive gas.

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29. The method of manufacturing a semiconductor device of claim 28, wherein

concentration of the components of said inert or reactive gas exceeds $1 \times 10^{20} \text{ cm}^{-3}$.

30. The method of manufacturing a semiconductor device
of claim 26, wherein

said first voltage is a negative voltage.

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31. The method of manufacturing a semiconductor device
of claim 26, wherein

said second voltage is a voltage of 0 V or lower.

10 32. The method of manufacturing a semiconductor device
of claim 26, wherein

said semiconductor substrate is composed of silicon,

said impurity is arsenic, phosphorus, boron, aluminum,
antimony, gallium, or indium, and

15 said inert or reactive gas is gas including nitrogen or
argon.

33. A method of manufacturing a semiconductor device,
comprising the steps of:

20 electrically isolating a transistor formation region on a
semiconductor substrate by an element isolation layer;

forming an electrode at said transistor formation region on said semiconductor substrate at which said element isolation layer is formed, with an insulating layer interposed therebetween;

5 holding, in a vacuum chamber, said semiconductor substrate at which said electrode is formed and an impurity solid including impurity to be introduced into said transistor formation region;

10 introducing inert or reactive gas into said vacuum chamber to generate plasma composed of said inert or reactive gas;

15 applying to said impurity solid a first voltage which allows said impurity solid to serve as an anode for said plasma, performing sputtering of said impurity solid by ions in said plasma, and thereby mixing said impurity in said impurity solid into said plasma;

20 applying to said semiconductor substrate held in said vacuum chamber a second voltage which allows said semiconductor substrate to serve as an anode for said plasma to cause a potential difference between said plasma and said semiconductor substrate so that said impurity mixed into said plasma is introduced directly to a surface portion of said

transistor formation region at said semiconductor substrate
to form an impurity layer; and

forming, on said semiconductor substrate at which said
impurity layer is formed, an interconnection layer

5 electrically connected to said impurity layer.

34. The method of manufacturing a semiconductor device
of claim 30, wherein

10 said step of introducing said impurity within said
plasma onto the surface of the diode formation region of said
semiconductor substrate includes, a process of irradiation of
a laser beam on said semiconductor substrate.

35. The method of manufacturing a semiconductor device
15 of claim 30, wherein

 said impurity layer includes components of said inert or
reactive gas.

36. The method of manufacturing a semiconductor device
20 of claim 35, wherein

 concentration of the components of said inert or
reactive gas exceeds $1 \times 10^{20} \text{ cm}^{-3}$.

37. The method of manufacturing a semiconductor device
of claim 30, wherein

each of said first and second voltages is a voltage of 0
V or lower.

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38. The method of manufacturing a semiconductor device
of claim 30, wherein

10 said semiconductor substrate is composed of silicon,
 said impurity is arsenic, phosphorus, boron, aluminum,
 antimony, gallium, or indium, and
 said inert or reactive gas is gas including nitrogen or
 argon.